

SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)									
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit			
Static									
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	20			٧			
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = 250 μA		24		mV/°C			
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	10 = 200 μΛ		- 5.6					
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	1		3	٧			
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA			
Zava Cata Valtaga Dvain Current	,	V _{DS} = 20 V, V _{GS} = 0 V			1	μΑ			
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			10				
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	20			Α			
	В	V _{GS} = 10 V, I _D = 7 A		0.0108	0.0135	Ω			
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 5 \text{ A}$		0.0146	0.0185				
Forward Transconductance ^a	9 _{fs}	V _{DS} = 10 V, I _D = 7 A		16		S			
Dynamic ^b	•								
Input Capacitance	C _{iss}			800					
Output Capacitance	C _{oss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		200		pF			
Reverse Transfer Capacitance	C _{rss}			90					
T. 10 . 0	Q_g	V _{DS} = 10 V, V _{GS} = 10 V, I _D = 12 A		12	18	nC			
Total Gate Charge		V _{DS} = 10 V, V _{GS} = 4.5 V, I _D = 12 A		5.3	9				
Gate-Source Charge	Q_{gs}			2					
Gate-Drain Charge	Q_{gd}			1.4					
Gate Resistance	R_{g}	f = 1 MHz		2.5		Ω			
Turn-On Delay Time	t _{d(on)}			16	25				
Rise Time	t _r	, 10 V D 10		10	15				
Turn-Off Delay Time	t _{d(off)}	$V_{DD} = 10 \text{ V}, R_L = 1 \Omega$ $I_D \cong 10 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_q = 1 \Omega$		15	25				
Fall Time	t _f	$\frac{10}{10} = 10 \text{ A}, \text{ VGEN} = 4.3 \text{ V}, \text{ Hg} = 1.52$		10	15				
Turn-On Delay Time	t _{d(on)}			10	15	ns			
Rise Time	t _r	1		8	15				
Turn-Off Delay Time	t _{d(off)}	$V_{DD} = 10 \text{ V}, R_L = 1 \Omega$ $I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_q = 1 \Omega$		17	30				
Fall Time	t _f	ID = 10 A, VGEN - 10 V, IIg - 122		8	15				
Drain-Source Body Diode Characteristic	es								
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			12	Α			
Pulse Diode Forward Current	I _{SM}				40				
Body Diode Voltage	V _{SD}	I _S = 5 A, V _{GS} = 0 V		0.8	1.2	V			
Body Diode Reverse Recovery Time	t _{rr}			18	30	ns			
Body Diode Reverse Recovery Charge	Q _{rr}	1 40 4 41/41 400 4/ 7 57 07		7	15	nC			
Reverse Recovery Fall Time	t _a	$I_F = 10 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$		8		ns			
Reverse Recovery Rise Time	t _b	1		10					

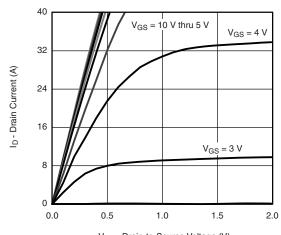
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

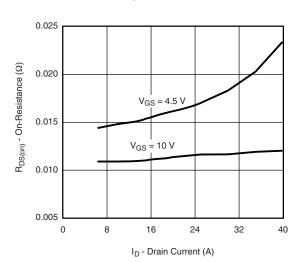


TYPICAL CHARACTERISTIC (25 °C, unless otherwise noted)

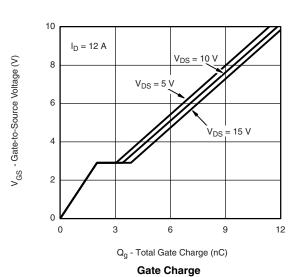


V_{DS} - Drain-to-Source Voltage (V)

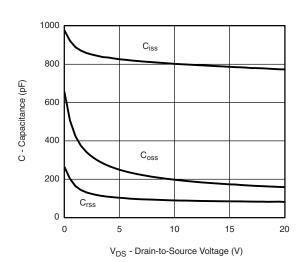
Output Characteristics



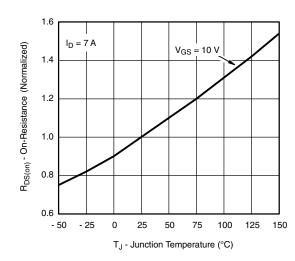
On-Resistance vs. Drain Current and Gate Voltage



V_{GS} - Gate-to-Source Voltage (V) **Transfer Characteristics**

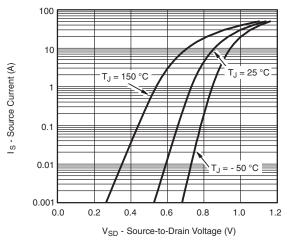


Capacitance

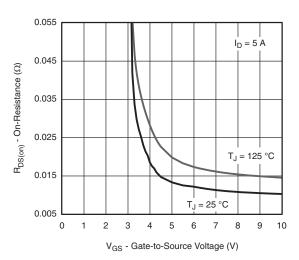


On-Resistance vs. Junction Temperature

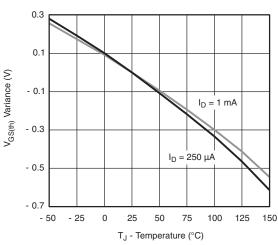
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



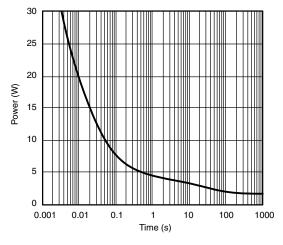
Source-Drain Diode Forward Voltage



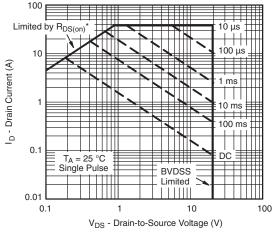
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power (Junction-to-Ambient)



 * V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

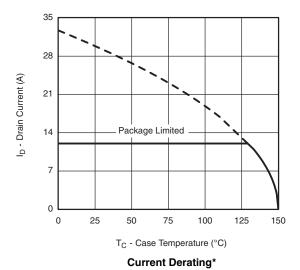
Safe Operating Area, Junction-to-Ambient

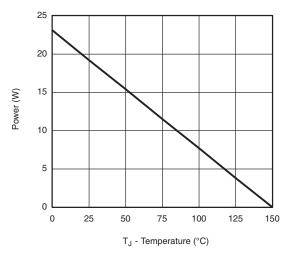






TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



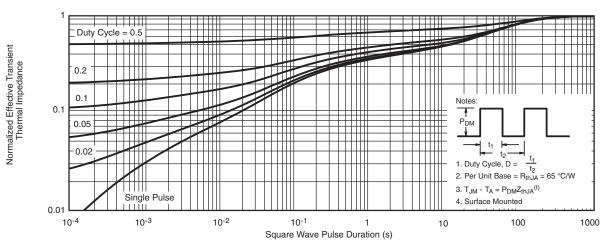


Power Derating

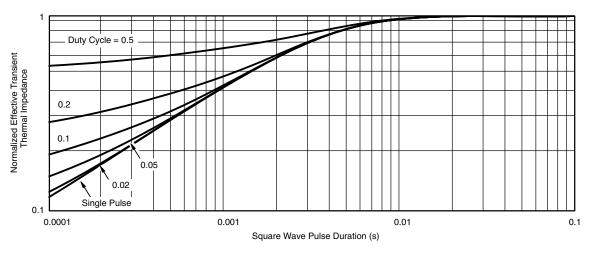
^{*} The power dissipation P_D is based on $T_{J(max.)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

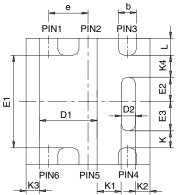


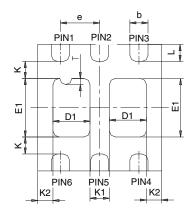
Normalized Thermal Transient Impedance, Junction-to-Case

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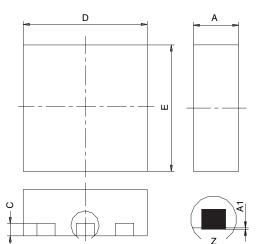
PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

DIM	SINGLE PAD					DUAL PAD						
	MILLIMETERS			INCHES		MILLIMETERS			INCHES			
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A 1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D2	0.135	0.235	0.335	0.005	0.009	0.013						
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E2	0.345	0.395	0.445	0.014	0.016	0.018						
E3	0.425	0.475	0.525	0.017	0.019	0.021						
е	0.65 BSC		0.026 BSC		0.65 BSC		0.026 BSC					
K	0.275 TYP		0.011 TYP		0.275 TYP		0.011 TYP					
K1		0.400 TYP	1	0.016 TYP			0.320 TYP			0.013 TYP		
K2		0.240 TYP	1	0.009 TYP			0.252 TYP			0.010 TYP		
К3		0.225 TYP	1	0.009 TYP								
K4		0.355 TYP 0.014 TYP										
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
Т							0.05	0.10	0.15	0.002	0.004	0.006

DETAIL Z

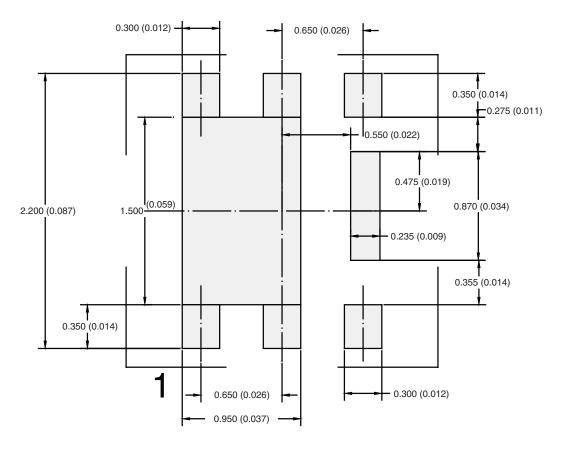
DWG: 5934

Document Number: 73001

06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

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